

# 60 V NPN/PNP low V<sub>CEsat</sub> (BISS) transistor Rev. 2 — 20 October 2010

Product data sheet

#### 1. **Product profile**

### **1.1 General description**

NPN/PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT96-1 (SO8) medium power Surface-Mounted Device (SMD) plastic package.

#### Table 1. **Product overview**

Type number	er Package		NPN/NPN	PNP/PNP	
	Nexperia	Name	complement	complement	
PBSS4041SPN	SOT96-1	SO8	PBSS4041SN	PBSS4041SP	

### 1.2 Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FF</sub>) at high I<sub>C</sub>
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

### 1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management

- Charging circuits
- Power switches (e.g. motors, fans)

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### 1.4 Quick reference data

#### Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1; NPN	low V <sub>CEsat</sub> transistor					
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	60	V
I <sub>C</sub>	collector current		-	-	6.7	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	15	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C} = 4 \text{ A}; I_{B} = 0.2 \text{ A}$	<u>[1]</u> -	32	48	mΩ

### 60 V NPN/PNP low V<sub>CEsat</sub> (BISS) transistor

Table 2.	Quick reference data continued							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
TR2; PNP	low V <sub>CEsat</sub> transistor							
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-60	V		
I <sub>C</sub>	collector current		-	-	-5.9	А		
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-15	А		
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C} = -4 \text{ A}; I_{B} = -0.4 \text{ A}$	[1] -	47	70	mΩ		

[1] Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02.$ 

### 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		8765
3	emitter TR2		
4	base TR2		
5	collector TR2		1 2 3 4
6	collector TR2		<i>006aaa985</i>
7	collector TR1		
8	collector TR1		

### 3. Ordering information

Table 4.         Ordering information							
Type number	Package						
	Name	Description	Version				
PBSS4041SPN	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1				

### 4. Marking

Table 5.	Marking codes	
Type num	ber	Marking code
PBSS404	1SPN	4041SPN

### 60 V NPN/PNP low V<sub>CEsat</sub> (BISS) transistor

### 5. Limiting values

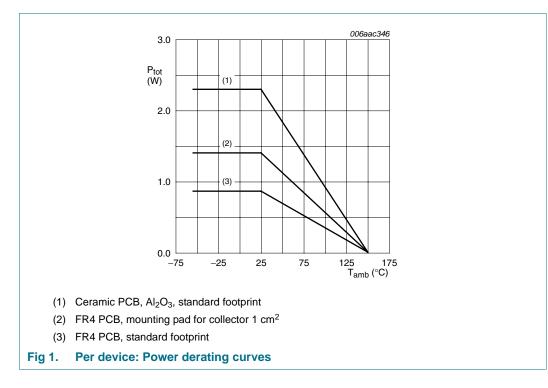
Symbol	Parameter	Conditions	Min	Мах	Unit
TR1 (NPN)					
I <sub>C</sub>	collector current		-	6.7	А
TR2 (PNP)					
I <sub>C</sub>	collector current		-	-5.9	А
Per transis	stor; for the PNP transistor	with negative polarity			
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	15	А
I <sub>B</sub>	base current		-	1	А
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	0.73	W
			[2] _	1	W
			[3] _	1.7	W
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	0.86	W
			[2] _	1.4	W
			[3] _	2.3	W
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

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### 6. Thermal characteristics

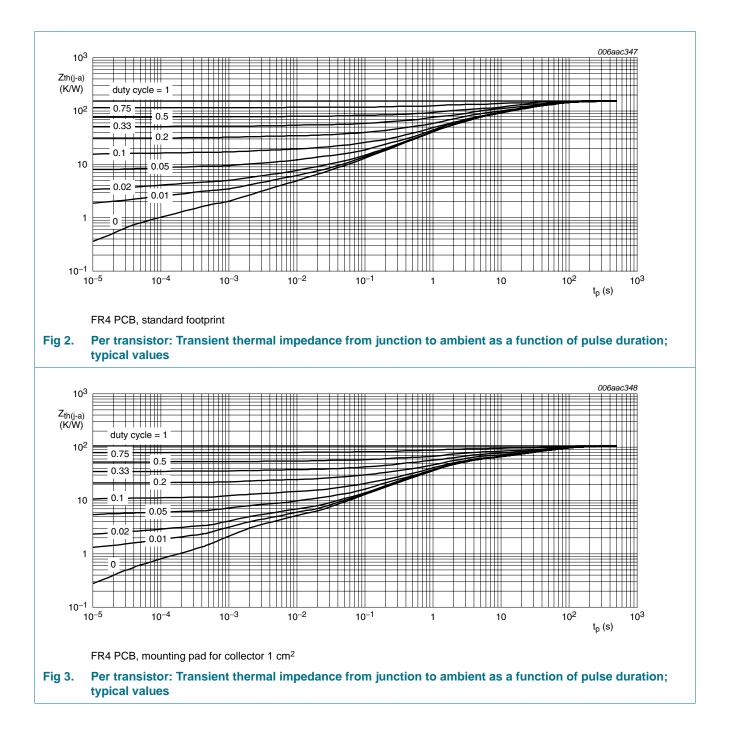
Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance from	in free air	<u>[1]</u> _	-	170	K/W
	junction to ambient		[2] _	-	125	K/W
			[3] _	-	75	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	40	K/W
Per devi	ce					
R <sub>th(j-a)</sub>	thermal resistance from	in free air	<u>[1]</u> _	-	145	K/W
	junction to ambient		[2] _	-	90	K/W
			[3]	-	55	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

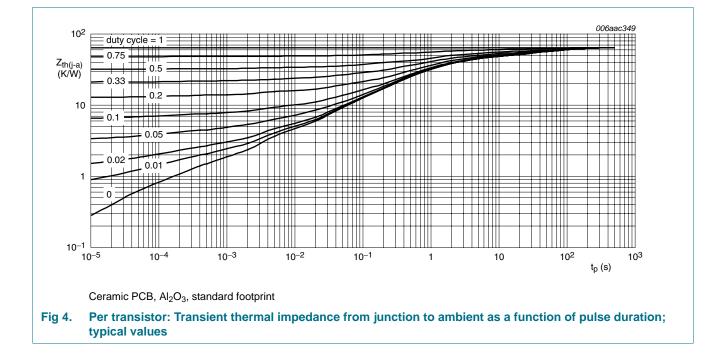
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

## PBSS4041SPN



### PBSS4041SPN



60 V NPN/PNP low V<sub>CEsat</sub> (BISS) transistor

### 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR1; NP	N low V <sub>CEsat</sub> transisto	r					
I <sub>CBO</sub>	collector-base	V <sub>CB</sub> = 60 V; I <sub>E</sub> = 0 A		-	-	100	nA
	cut-off current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = 48 V; $V_{BE}$ = 0 V		-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 V; I_{C} = 0 A$		-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 2 V$	[1]				
		I <sub>C</sub> = 500 mA		300	500	-	
		$I_{\rm C} = 1  {\rm A}$		300	500	-	
		$I_{\rm C} = 2  {\rm A}$		250	450	-	
		$I_{\rm C} = 4$ A		150	250	-	
		I <sub>C</sub> = 6 A		75	150	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage		[1]				
		$I_{C} = 1 \text{ A}; I_{B} = 50 \text{ mA}$		-	40	60	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 10 mA		-	65	100	mV
		$I_{C} = 2 \text{ A}; I_{B} = 40 \text{ mA}$		-	85	145	mV
		$I_{C} = 4 \text{ A}; I_{B} = 200 \text{ mA}$		-	125	190	mV
		$I_{C} = 4 \text{ A}; I_{B} = 40 \text{ mA}$		-	220	320	mV
		I <sub>C</sub> = 7 A; I <sub>B</sub> = 350 mA		-	230	350	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C} = 4 \text{ A}; I_{B} = 200 \text{ mA}$	<u>[1]</u>	-	32	48	mΩ
V <sub>BEsat</sub>	base-emitter		[1]				
	saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA		-	0.86	1	V
		I <sub>C</sub> = 4 A; I <sub>B</sub> = 400 mA		-	1.05	1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 2 \text{ A}$	<u>[1]</u>	-	0.75	0.85	V
t <sub>d</sub>	delay time	$V_{CC}$ = 12.5 V; I <sub>C</sub> = 1 A;		-	35	-	ns
t <sub>r</sub>	rise time	I <sub>Bon</sub> = 0.05 A; I <sub>Boff</sub> = -0.05 A		-	65	-	ns
t <sub>on</sub>	turn-on time			-	100	-	ns
t <sub>s</sub>	storage time			-	1050	-	ns
t <sub>f</sub>	fall time			-	220	-	ns
t <sub>off</sub>	turn-off time			-	1270	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 100 \text{ mA};$ f = 100 MHz		-	130	-	MHz
C <sub>c</sub>	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 10 \; V; \; I_{E} = i_{e} = 0 \; A; \\ f = 1 \; MHz \end{array}$		-	35	-	pF

PBSS4041SPN Product data sheet

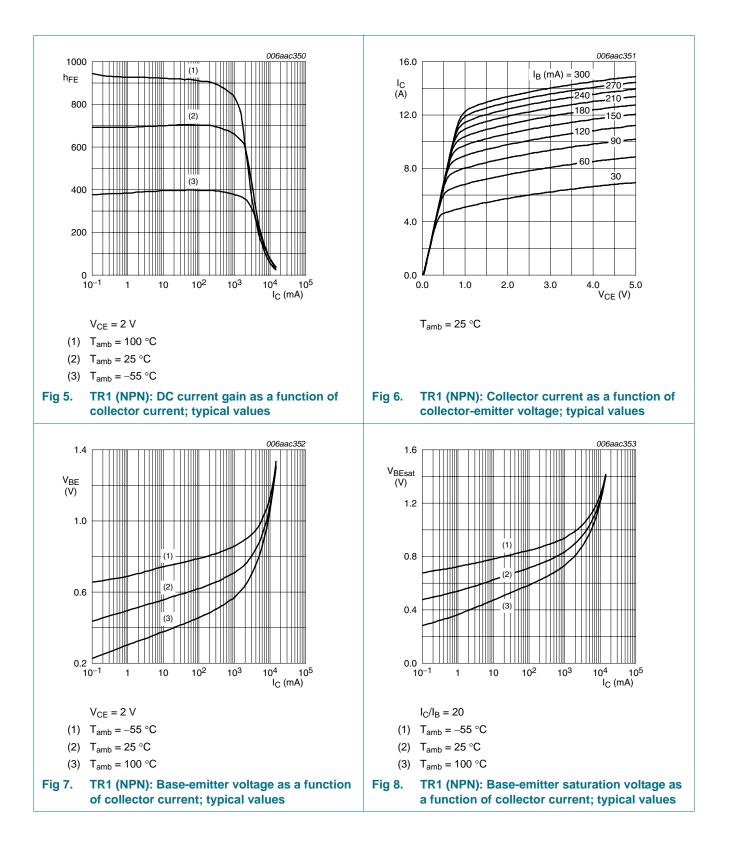
### 60 V NPN/PNP low V<sub>CEsat</sub> (BISS) transistor

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
TR2; PN	P low V <sub>CEsat</sub> transisto	r					
I <sub>CBO</sub>	collector-base	$V_{CB} = -60 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	cut-off current	$\label{eq:V_CB} \begin{split} V_{CB} &= -60 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \\ T_{j} &= 150 ^{\circ}\text{C} \end{split}$		-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -48 \text{ V};  V_{BE} = 0 \text{ V}$		-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 V$	[1]				
		I <sub>C</sub> = -500 mA		200	300	-	
		$I_{\rm C} = -1$ A		180	270	-	
		$I_{\rm C} = -2  {\rm A}$		150	250	-	
		$I_{C} = -4 A$		120	180	-	
		I <sub>C</sub> = -6 A		80	125	-	
V <sub>CEsat</sub>	collector-emitter		<u>[1]</u>				
	saturation voltage	$I_{\rm C} = -1$ A; $I_{\rm B} = -50$ mA		-	-65	-90	mV
		$I_{\rm C} = -1$ A; $I_{\rm B} = -10$ mA		-	-130	-190	mV
		$I_{\rm C} = -2$ A; $I_{\rm B} = -40$ mA		-	-155	-230	mV
		$I_{C} = -4 \text{ A}; I_{B} = -200 \text{ mA}$		-	-220	-330	mV
		$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$		-	-190	-275	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$	<u>[1]</u>	-	47	70	mΩ
V <sub>BEsat</sub>	base-emitter		[1]				
	saturation voltage	$I_{C} = -1 \text{ A}; I_{B} = -100 \text{ mA}$		-	-0.84	-1	V
		$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$		-	-1	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -2 \text{ A}$	<u>[1]</u>	-	-0.78	-0.85	V
t <sub>d</sub>	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -1 \text{ A};$		-	45	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = -0.05 \text{ A}; I_{Boff} = 0.05 \text{ A}$		-	60	-	ns
t <sub>on</sub>	turn-on time			-	105	-	ns
t <sub>s</sub>	storage time			-	440	-	ns
t <sub>f</sub>	fall time			-	75	-	ns
t <sub>off</sub>	turn-off time			-	515	-	ns
f <sub>T</sub>	transition frequency	$V_{CB} = -10 \text{ V}; I_{C} = -100 \text{ mA};$ f = 100 MHz		-	110	-	MH
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	85	-	pF

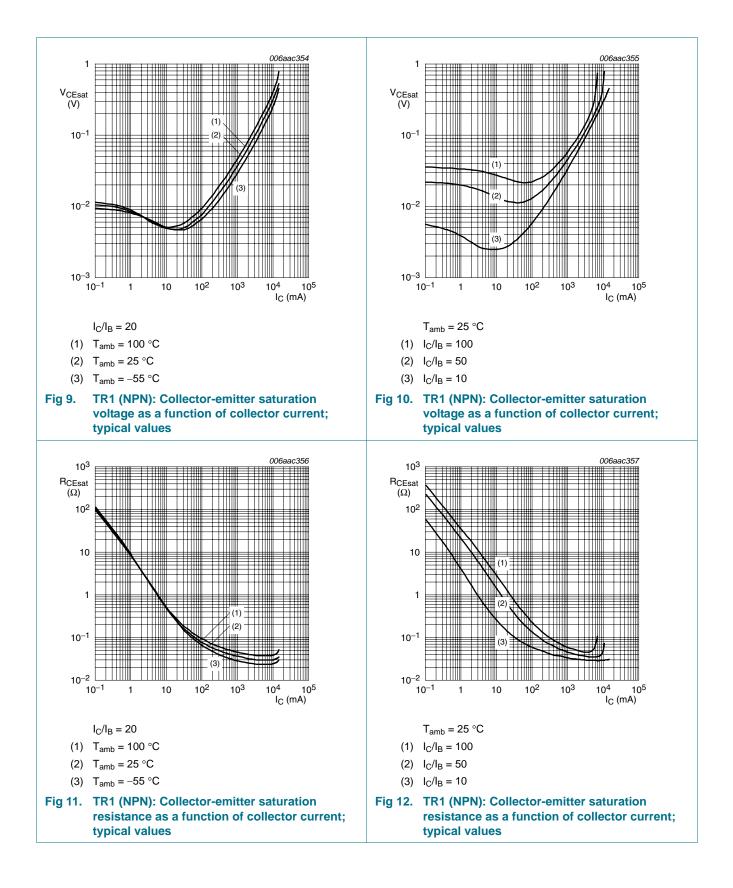
### Table 8. Characteristics ...continued

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .

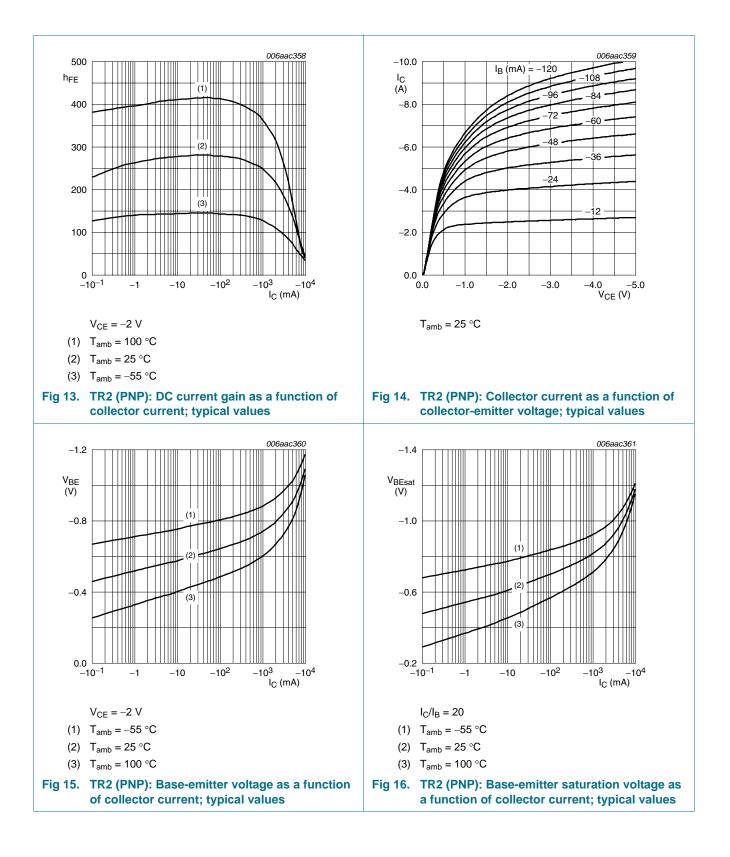
### PBSS4041SPN



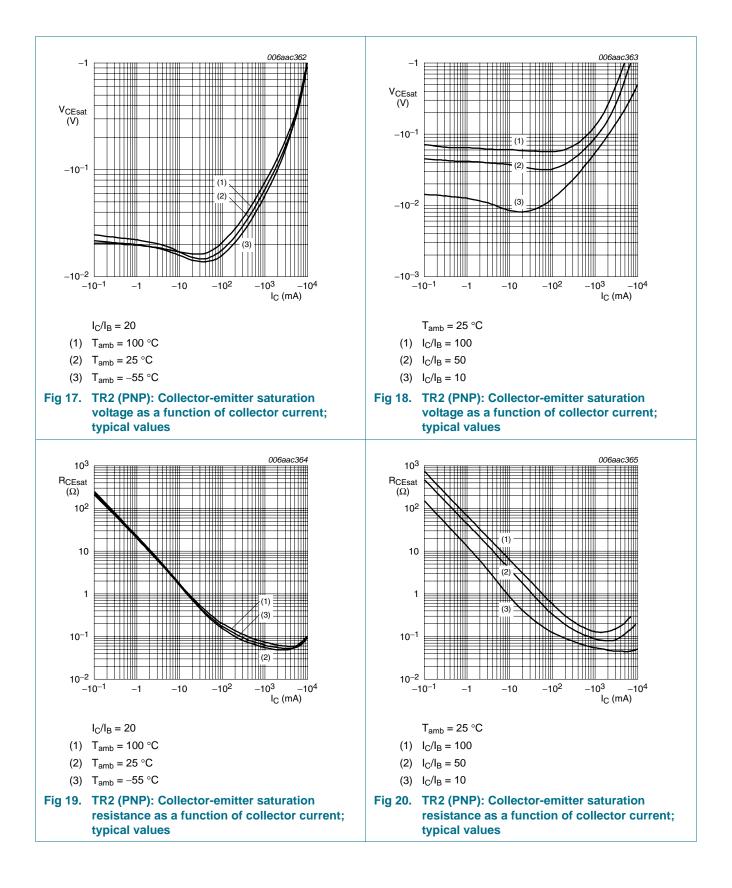
## PBSS4041SPN



## PBSS4041SPN

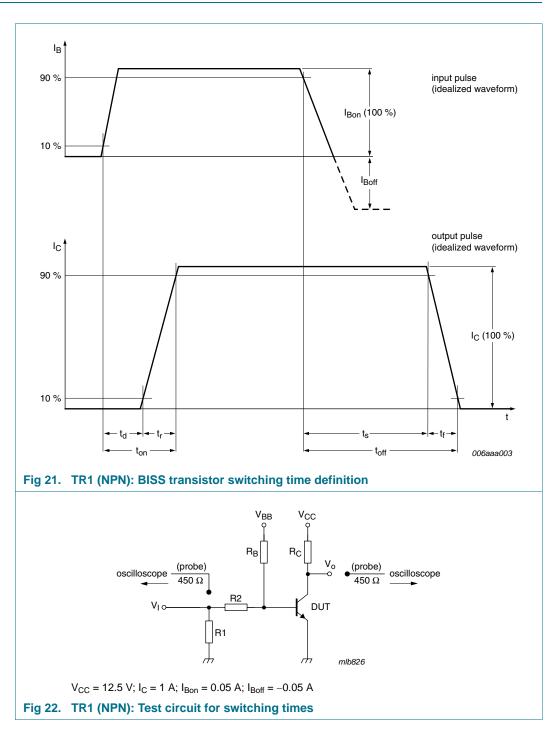


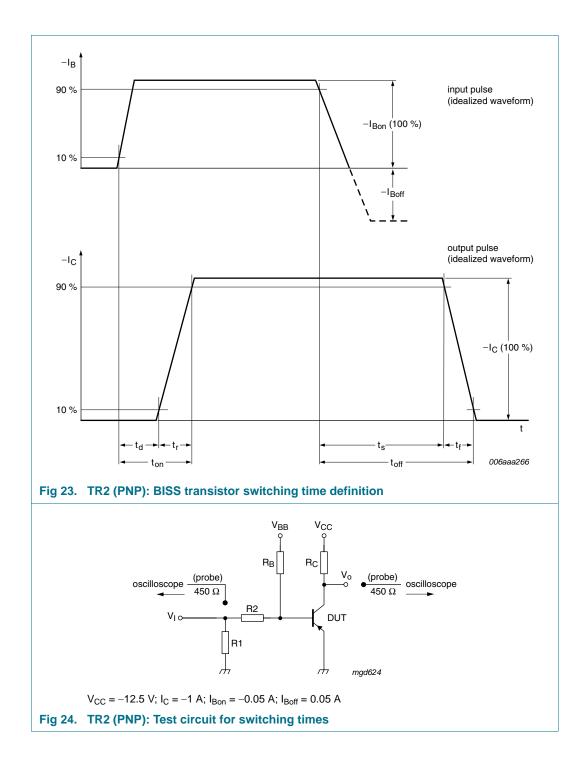
## PBSS4041SPN



60 V NPN/PNP low V<sub>CEsat</sub> (BISS) transistor

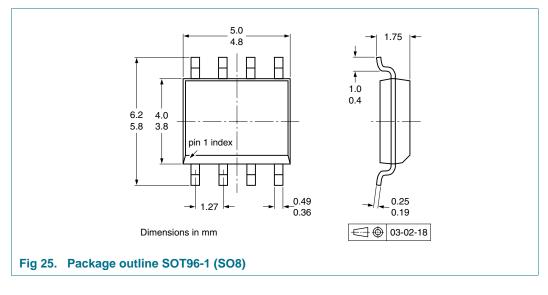
### 8. Test information





60 V NPN/PNP low V<sub>CEsat</sub> (BISS) transistor

### 9. Package outline



### **10. Packing information**

#### Table 9. Packing methods

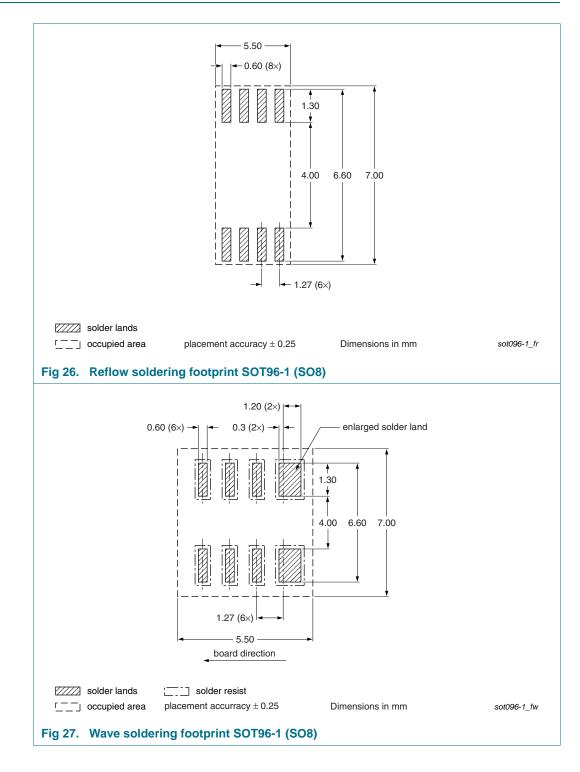
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package Description Packing quantity			
			1000	2500
PBSS4041SPN	SOT96-1	8 mm pitch, 12 mm tape and reel	-115	-118

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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### **11. Soldering**



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### **12. Revision history**

Table 10. Revision hi	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4041SPN v.2	20101020	Product data sheet	-	PBSS4041SPN v.1
Modifications:	Figure 1 "Pe	er device: Power derating cu	irves": updated.	
PBSS4041SPN v.1	20100714	Product data sheet	-	-

#### 60 V NPN/PNP low V<sub>CEsat</sub> (BISS) transistor

### 13. Legal information

### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nexperia.com">http://www.nexperia.com</a>.

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**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

#### 13.4 Trademarks

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### 14. Contact information

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